What is claimed is:

1. A method comprising:

soaking a substrate having a dielectric deposited thereon in a salt solution; and

depositing an oxide on said dielectric.

2. The method of claim 1 wherein depositing an oxide on said dielectric includes depositing aluminum oxide on said dielectric.

3. The method of claim 1 wherein soaking said substrate in said salt solution includes soaking said substrate in a salt solution comprising an aluminum salt.

4. The method of 3 wherein soaking said substrate in said salt solution comprising said aluminum salt includes soaking said substrate in a salt solution comprising aluminum chloride dissolved in water.

5. The method of 3 wherein soaking said substrate in said salt solution comprising said aluminum salt includes soaking said substrate in a salt solution comprising aluminum nitrate dissolved in water.

6. The method of claim 3 wherein soaking said substrate in said salt solution comprising said aluminum salt includes causing the reactants in said aluminum salt

solution available for surface reaction to range from about a few parts per million to about one percent.

7. The method of claim 1 wherein soaking said substrate in said salt solution includes adjusting the pH of said salt solution.

8. The method of claim 1 wherein depositing said oxide on said dielectric includes depositing said oxide on silicon dioxide.

9. The method of claim 1 wherein depositing said oxide on said dielectric includes depositing said oxide on hafnium oxide.

10. The method of claim 1 including depositing a gate material on said oxide.

11. A method comprising:

preparing a salt solution;

exposing a dielectric deposited on a substrate to said salt solution; and

causing an oxide to deposit on said dielectric.

12. The method of claim 11 wherein preparing said salt solution includes preparing an aluminum salt solution.

13. The method of claim 12 wherein preparing said aluminum salt solution includes preparing an aluminum chloride solution.

14. The method of claim 12 wherein preparing said aluminum salt solution includes preparing an aluminum nitrate solution.

15. The method of claim 12 wherein preparing said aluminum salt solution includes adjusting the pH of said aluminum salt solution.

16. The method of claim 12 wherein causing an oxide to deposit on said dielectric includes causing reactants in said aluminum salt solution to react with the top surface of said dielectric.

17. The method of claim 16 wherein causing said reactants in said aluminum salt solution to react with the top surface of said dielectric includes depositing an aluminum oxide layer ranging in thickness from about a few parts per million to one or more atomic layers.

18. The method of claim 11 wherein exposing said dielectric to said salt solution includes exposing a

dielectric selected from the group consisting of silicon dioxide, hafnium dioxide and zirconia to said salt solution.

19. The method of claim 11 including removing said substrate from said salt solution and rinsing.

20. The method of claim 11 wherein exposing said dielectric to said salt solution includes exposing said dielectric to said salt solution for about a few seconds to about an hour.

21. A method comprising:

depositing a dielectric on a substrate; and

causing an oxide to deposit on said dielectric by immersing said substrate in a salt solution.

22. The method of claim 21 wherein depositing a dielectric on said substrate includes depositing an oxide on said substrate.

23. The method of claim 22 wherein depositing said oxide on said substrate includes depositing hafnium oxide on said substrate.

24. The method of claim 22 wherein depositing said oxide on said substrate includes depositing zirconia on said substrate.

25. The method of claim 22 wherein depositing said oxide on said substrate includes depositing silicon dioxide on said substrate.

26. The method of claim 21 wherein causing an oxide to deposit on said dielectric by immersing said substrate in a salt solution includes causing aluminum oxide to deposit on said dielectric by immersing said substrate in an aluminum salt solution.

27. The method of claim 26 wherein causing said aluminum oxide to deposit on said dielectric includes causing about a few parts per million of aluminum oxide to one or more atomic layers of aluminum oxide to deposit on said dielectric.

28. The method of claim 26 including adjusting the pH of said aluminum salt solution.

29. The method of claim 26 wherein causing aluminum oxide to deposit on said dielectric by immersing said substrate in said aluminum salt solution includes causing

the top surface of said dielectric to react with reactants in said aluminum salt solution.

30. The method of claim 21 including a forming a gate material on said oxide.